SOT89 PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

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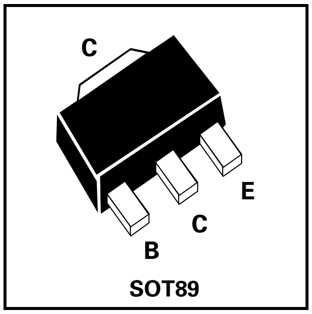
BCX5316



COMPLIMENTARY TYPE – BCX5616

PARTMARKING DETAIL – AL

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1.5	A
Continuous Collector Current	I_C	-1	A
Power Dissipation at T_{amb}=25°C	P_{tot}	1	W
Operating and Storage Temperature Range	T_j:T_{stg}	-65 to +150	°C

ELECTRICAL CHARACTERISTICS (at T_{amb} = 25°C unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown voltage	$V_{(BR)CBO}$	-100			V	IC =-100µA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80			V	IC =-10mA
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	I_E =-10µA
Collector Cut-Off Current	I_{CBO}			-0.1 -20	µA µA	V_{CB} =-30V V_{CB} =-30V, T_{amb} =150°C
Emitter Cut-Off Current	I_{EBO}			-10	µA	V_{EB} =-4V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	I_C =-500mA, I_B =-50mA*
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	I_C =-500mA, V_{CE} =-2V*
Static Forward Current Transfer Ratio	h_{FE}	25 100 25		 250 		I_C =-5mA, V_{CE} =-2V* I_C =-150mA, V_{CE} =-2V* I_C =-500mA, V_{CE} =-2V*
Transition Frequency	f_T	150			MHz	I_C =-50mA, V_{CE} =-10V, f=100MHz
Output Capacitance	C_{obo}			25	pF	V_{CB} =-10V, f=1MHz

*Measured under pulsed conditions.

ZETEX